μESD3.3DT5G SERIES

ESD Protection Diodes

In Ultra Small SOT−723 Package

The μESD Series is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, portable devices, digital cameras, power supplies and many other portable applications.

Specification Features:

- Small Body Outline Dimensions:
  0.047″ x 0.032″ (1.20 mm x 0.80 mm)
- Low Body Height: 0.020″ (0.5 mm)
- Stand−off Voltage: 3.3 V − 6.0 V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000−4−2 Level 4 ESD Protection
- IEC61000−4−4 Level 4 EFT Protection
- These are Pb−Free Devices

Mechanical Characteristics:

CASE: Void−free, transfer−molded, thermosetting plastic Epoxy Meets UL 94 V−0
LEAD FINISH: 100% Matte Sn (Tin)
MOUNTING POSITION: Any
QUALIFIED MAX REFLOW TEMPERATURE: 260°C
Device Meets MSL 1 Requirements

MAXIMUM RATINGS

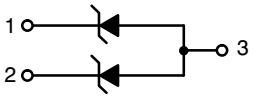
Rating	Symbol	Value	Unit
IEC 61000−4−2 (ESD) Air Contact		±30 ±30	kV
IEC 61000−4−4 (EFT)		40	A
ESD Voltage Per Human Body Model Per Machine Model		16 400	kV V
Total Power Dissipation on FR−5 Board (Note 1) @ T_A = 25°C Derate above 25°C Thermal Resistance Junction−to−Ambient	 P_D $R_{\theta JA}$	 240 1.9 525	 mW mW/°C °C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C
Lead Solder Temperature − Maximum (10 Second Duration)	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
1. FR−5 = 1.0 x 0.75 x 0.62 in.

ON Semiconductor®

http://onsemi.com

PIN 1. CATHODE
2. CATHODE
3. ANODE



SOT−723
CASE 631AA
STYLE 4

MARKING DIAGRAM

xx = Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
μESDxxDT5G	SOT−723	8000/Tape & Reel

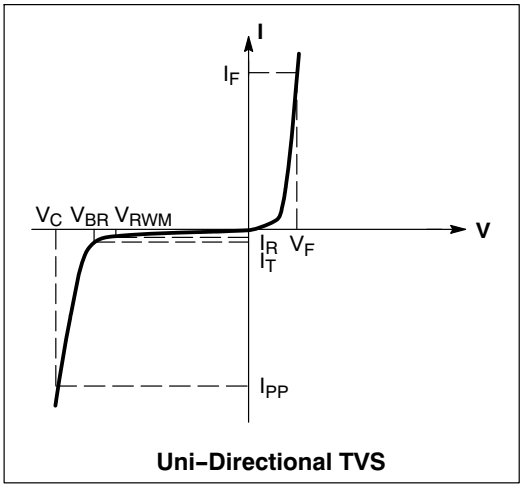
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS
(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F
P_{pk}	Peak Power Dissipation
C	Max. Capacitance @V_R = 0 and f = 1 MHz



Uni−Directional TVS

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, V_F = 1.1 V Max. @ I_F = 10 mA for all types)

Device*	Device Marking	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 2)	I_T	C (pF)
		Max	Max	Min	mA	Typ
μESD3.3DT5G	L0	3.3	1.0	5.0	1.0	47
μESD5.0DT5G	L2	5.0	0.1	6.2	1.0	38
μESD6.0DT5G	L3	6.0	0.1	7.0	1.0	34

*Other voltages available upon request.
2. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

TYPICAL CHARACTERISTICS

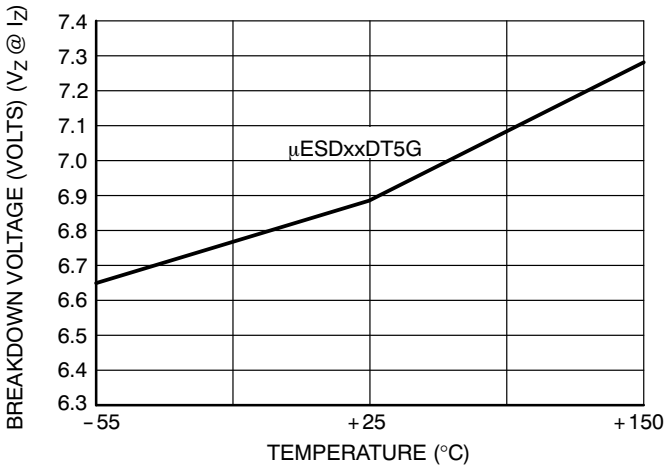


Figure 1. Typical Breakdown Voltage versus Temperature

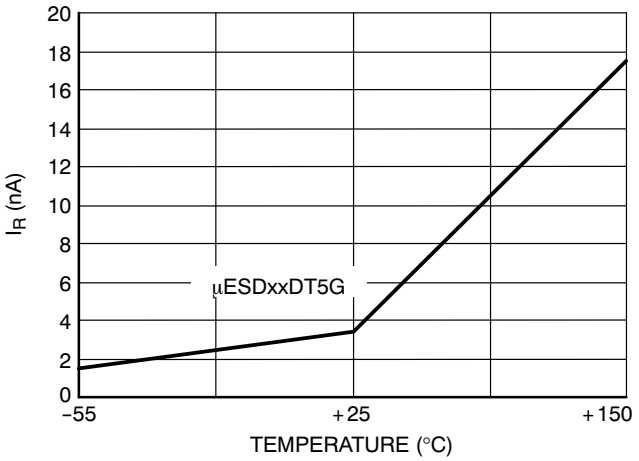


Figure 2. Typical Leakage Current versus Temperature

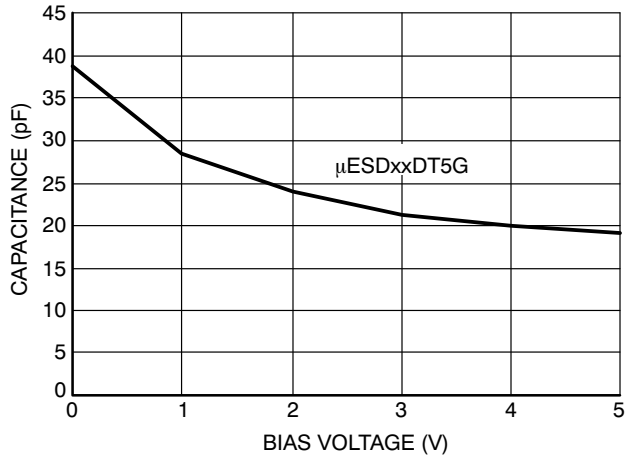


Figure 3. Typical Capacitance versus Bias Voltage

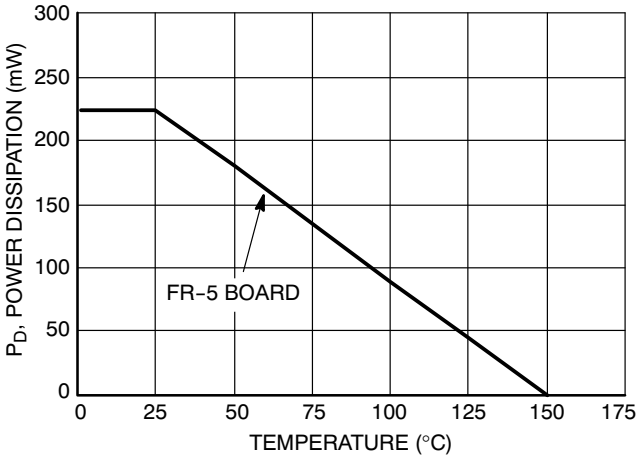


Figure 4. Steady State Power Derating Curve

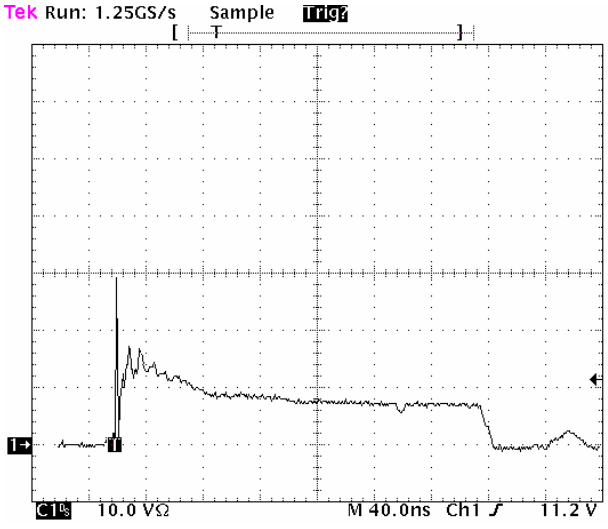


Figure 5. Positive 8 kV contact per IEC 6100−4−2 − μESD5.0DT5G

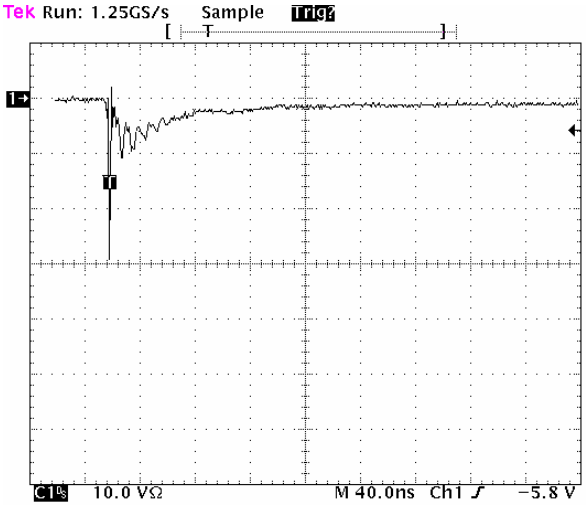
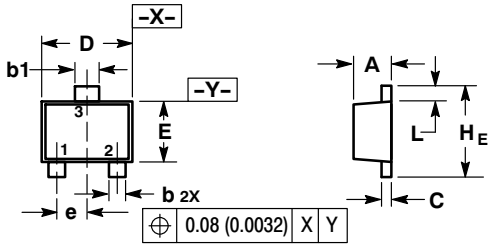


Figure 6. Negative 8 kV contact per IEC 61000−4−2 − μESD5.0DT5G

μESD3.3DT5G SERIES

PACKAGE DIMENSIONS

SOT−723
CASE 631AA−01
ISSUE A

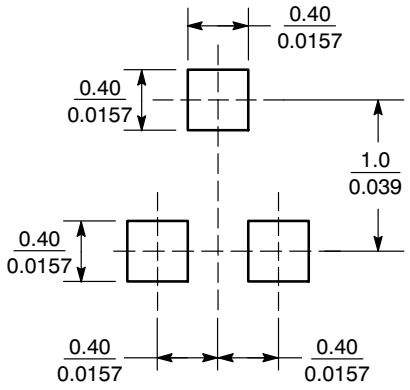


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.20	0.27	0.0059	0.0079	0.0106
b1	0.25	0.3	0.35	0.010	0.012	0.014
C	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC			0.016 BSC		
H E	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

SOLDER FOOTPRINT*



SCALE 20:1 $\left(\frac{mm}{inches}\right)$

SOT−723

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative